



Packet No. 215878US99DIV

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Jamal Ramdani et al

SERIAL NO: 09/986,034 ✓

GAU: 2815

FILED: November 7, 2001 ✓

EXAMINER:

FOR: SEMICONDUCTOR STRUCTURE, SEMICONDUCTOR DEVICE, COMMUNICATING DEVICE, INTEGRATED CIRCUIT, AND PROCESS FOR FABRICATING THE SAME

2815
#5/I.D.
4/8/03
Smith

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.

Richard L. Treanor

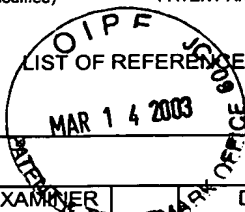
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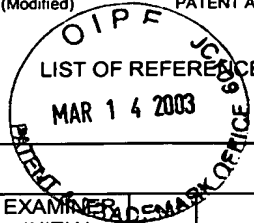


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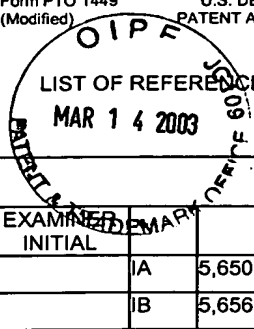
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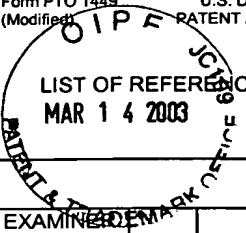
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 LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Jamal Ramdani et al			
				FILING DATE November 7, 2001		GROUP 2815	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
AA	3,802,967	04/09/74	Ladany et al.				
AB	4,174,422	11/13/79	Matthews et al.				
AC	4,404,265	09/13/83	Manasevit				
AD	4,482,906	11/13/84	Hovel et al.				
AE	4,523,211	06/11/85	Morimoto et al.				
AF	4,661,176	04/28/87	Manasevit				
AG	4,793,872	12/27/88	Meunier et al.				
AH	4,846,926	07/11/89	Kay et al.				
AJ	4,855,249	08/08/89	Akasaki et al.				
AI	4,891,091	01/02/90	Shastri				
AK	4,912,087	03/27/90	Aslam et al.				
AL	4,928,154	05/22/90	Umeno et al.				
AM	4,963,949	10/16/90	Wanlass et al.				
AN	5,141,894	08/25/92	Bisaro et al.				
AO	5,159,413	10/27/92	Calviello et al.				
AP	5,173,474	12/22/92	Connell et al.				
AQ	5,221,367	06/22/93	Chisholm et al.				
AR	5,225,031	07/06/93	McKee et al.				
AS	5,358,925	10/25/94	Neville Connell et al.				
AT	5,393,352	02/28/95	Summerfelt				
AU	5,418,216	05/23/95	Fork				
AV	5,450,812	09/19/95	McKee et al.				
AW	5,478,653	12/26/95	Guenzer				
AX	5,482,003	01/09/96	McKee et al.				
AY	5,514,484	05/07/96	Nashimoto				
AZ	5,556,463	09/17/96	Guenzer				
BA	5,588,995	12/31/96	Sheldon				
BB	5,670,798	09/23/97	Schetzina				
BC	5,733,641	03/31/98	Fork et al.				
BD	5,735,949	04/07/98	Mantl et al.				
BE	5,741,724	04/21/98	Ramdani et al.				
BF	5,810,923	09/22/98	Yano et al.				
BG	5,830,270	11/03/98	McKee et al.				
BH	5,912,068	06/15/99	Jia				
BI	6,020,222	02/01/00	Wollesen				
BJ	6,045,626	04/04/00	Yano et al.				
BK	6,064,078	05/16/00	Northrup et al.				
BL	6,064,092	05/16/00	Park				
BM	6,096,584	08/01/00	Ellis-Monaghan et al.				
BN	6,103,008	08/15/00	McKee et al.				
BO	6,136,666	10/24/00	So				
BP	6,174,755	01/16/01	Manning				
BQ	6,180,486	01/30/01	Leobandung et al.				

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
CA	3,766,370	10/16/73	Walther				
CB	4,006,989	02/08/77	Andringa				
CC	4,284,329	08/18/81	Smith et al.				
CD	4,777,613	10/11/98	Shahan et al.				
CE	4,802,182	01/31/89	Thornton et al.				
CF	4,882,300	11/21/89	Inoue et al.				
CG	4,896,194	01/23/90	Suzuki				
CH	4,999,842	03/12/91	Huang et al.				
CI	5,081,062	01/14/92	Vasudev et al.				
CJ	5,155,658	10/13/92	Inam et al.				
CK	5,248,564	09/28/93	Ramesh				
CL	5,260,394	11/09/93	Tazaki et al.				
CM	5,270,298	12/14/93	Ramesh				
CN	5,286,985	02/15/94	Taddiken				
CO	5,310,707	05/10/94	Oishi et al.				
CP	5,326,721	07/05/94	Summerfelt				
CQ	5,404,581	04/04/95	Honjo				
CR	5,418,389	05/23/95	Watanabe				
CS	5,436,759	07/25/95	Dijai et al.				
CT	5,576,879	11/19/96	Nashimoto				
CU	5,606,184	02/25/97	Abrokwah, et al.				
CV	5,640,267	06/17/97	May et al.				
CW	5,674,366	10/07/97	Hayashi et al.				
CX	5,729,641	03/17/98	Chandonnet et al.				
CY	5,790,583	08/04/98	Ho				
CZ	5,825,799	10/20/98	Ho et al.				
DA	5,857,049	01/05/99	Beranek et al.				
DB	5,874,860	02/23/99	Brunel et al.				
DC	5,926,496	07/20/99	Ho et al.				
DD	5,937,285	08/10/99	Abrokwah, et al.				
DE	5,981,400	11/09/99	Lo				
DF	5,990,495	11/23/99	Ohba				
DG	6,002,375	12/14/99	Corman et al.				
DH	6,008,762	12/28/99	Nghiem				
DI	6,055,179	04/25/00	Koganei et al.				
DJ	6,107,653	08/22/00	Fitzgerald				
DK	6,113,690	09/05/00	Yu et al.				
DL	6,114,996	09/05/00	Nghiem				
DM	6,121,642	09/19/00	Newns				
DN	6,128,178	10/03/00	Newns				
DO	6,143,072	11/07/00	McKee et al.				
DP	6,184,144	02/06/01	Lo				
DQ	6,222,654	04/24/01	Frigo				

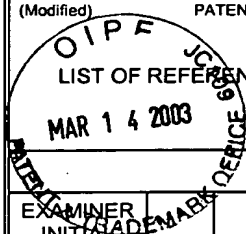
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LIST OF REFERENCES CITED BY APPLICANT MAR 14 2003 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				APPLICANT Jamal Ramdani et al		GROUP 2815	
				FILING DATE November 7, 2001			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	EA	4,484,332	11/20/84	Hawrylo			
	EB	4,815,084	03/21/89	Scifres et al.			
	EC	4,876,219	10/24/89	Eshita et al.			
	ED	4,963,508	10/16/90	Umeno et al.			
	EE	5,060,031	10/22/91	Abrokwah, et al.			
	EF	5,063,166	11/05/91	Mooney et al.			
	EG	5,116,461	05/26/92	Lebby et al.			
	EH	5,127,067	06/30/92	Delcoco et al.			
	EI	5,144,409	09/01/92	Ma			
	EJ	5,293,050	03/08/94	Chapple-Sokol et al			
	EK	5,356,831	10/18/94	Calviello et al.			
	EL	5,391,515	02/21/95	Kao et al.			
	EM	5,442,191	08/15/95	Ma			
	EN	5,444,016	08/22/95	Abrokwah, et al.			
	EO	5,480,829	01/02/96	Abrokwah, et al.			
	EP	5,528,414	06/18/96	Oakley			
	EQ	5,614,739	03/25/97	Abrokwah et al.			
	ER	5,729,394	03/17/98	Sevier et al.			
	ES	5,731,220	03/24/98	Tsu et al.			
	ET	5,764,676	06/09/98	Paoli et al.			
	EU	5,777,762	07/07/98	Yamamoto			
	EV	5,778,018	07/07/98	Yoshikawa et al.			
	EW	5,778,116	07/07/98	Tomich			
	EX	5,801,105	09/01/98	Yano et al.			
	EY	5,828,080	10/27/98	Yano et al.			
	EZ	5,858,814	01/12/99	Goossen et al.			
	FA	5,861,966	01/19/99	Ortel			
	FB	5,883,996	03/16/99	Knapp et al.			
	FC	5,995,359	11/30/99	Klee et al.			
	FD	6,058,131	05/02/00	Pan			
	FE	6,137,603	10/24/00	Henmi			
	FF	6,146,906	11/14/00	Inoue et al.			
	FG	6,173,474	01/16/01	Conrad			
	FH	6,180,252	01/30/01	Farrell et al.			
	FI	4,242,595	12/30/0	Lehovec			
	FJ	4,398,342	08/16/83	Pitt et al.			
	FK	4,424,589	01/03/84	Thomas et al.			
	FL	4,876,208	10/24/89	Gustafson et al.			
	FM	4,482,422	11/84	McGinn et al.			
	FN	4,667,088	05/19/87	Kramer			
	FO	4,772,929	09/20/88	Manchester et al.			
	FP	4,841,775	06/27/89	Ikeda et al.			
	FQ	4,845,044	07/04/89	Ariyoshi et al.			

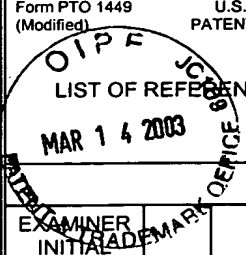
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	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
	HI	5,515,810	05/14/96	Yamashita et al.			
	HJ	5,519,235	05/96	Ramesh			
	HK	5,549,977	08/96	Jin et al.			
	HL	5,551,238	09/03/96	Prueitt			
	HM	5,552,547	09/03/96	Shi			
	HN	5,589,284	12/31/96	Summerfelt et al.			
	HO	5,602,418	02/11/97	Imai et al.			
	HP	5,633,724	05/27/97	King et al.			

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IA	5,650,646	07/22/97	Summerfelt				
IB	5,656,382	08/12/97	Nashimoto				
IC	5,659,180	08/19/97	Shen et al.				
ID	5,661,112	08/26/97	Hatta et al.				
IE	5,679,965	11/95	Schetzina				
IF	5,725,641	03/10/98	MacLeod				
IG	5,745,631	04/28/98	Reinker				
IH	5,776,621	07/07/98	Nashimoto				
II	5,777,350	07/07/98	Nakamura et al.				
IJ	5,789,845	08/04/98	Wadaka et al.				
IK	5,792,569	08/11/98	Sun et al.				
IL	5,792,679	08/11/98	Nakato				
IM	5,796,648	08/18/98	Kawakubo et al.				
IN	5,801,072	09/01/98	Barber				
IO	5,812,272	09/22/98	King et al.				
IP	5,814,583	09/98	Itozaki et al.				
IQ	5,825,055	10/20/98	Summerfelt				
IR	5,827,755	10/27/98	Yonchara et al.				
IS	5,833,603	11/10/98	Kovacs et al.				
IT	5,838,035	11/17/98	Ramesh				
IU	5,844,260	12/01/98	Ohori				
IV	5,846,846	12/08/98	Suh et al.				
IW	5,863,326	01/26/99	Nause et al.				
IX	5,872,493	02/16/99	Ella				
IY	5,879,956	03/99	Seon et al.				
IZ	5,880,452	03/09/99	Plesko				
JA	5,883,564	03/16/99	Partin				
JB	5,907,792	05/25/99	Droopad et al.				
JC	5,937,274	08/10/99	Kondow et al.				
JD	5,948,161	09/07/99	Kizuki				
JE	5,959,879	09/28/99	Koo				
JF	5,966,323	10/99	Chen et al.				
JG	5,987,011	11/16/99	Toh				
JH	6,022,140	02/08/00	Fraden et al.				
JI	6,022,410	02/08/00	Yu et al.				
JJ	6,023,082	02/08/00	McKee et al.				
JK	6,028,853	02/22/00	Haartsen				
JL	6,049,702	04/11/00	Tham et al.				
JM	6,078,717	06/20/00	Nashimoto et al				
JN	6,088,216	07/00	Laibowitz et al.				
JO	6,090,659	07/00	Laibowitz et al.				
JP	6,107,721	08/22/00	Lakin				
JQ	6,153,010	11/28/00	Kiyoku et al				

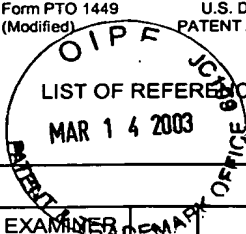
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KA	6,153,454	11/28/00	Krivokapic				
KB	6,191,011	02/01	Gilboa et al				
KC	6,204,737	03/20/01	Ella				
KD	6,224,669	05/01/01	Yi et al.				
KE	6,225,051	05/01/01	Sugiyama et al.				
KF	6,241,821	06/05/01	Yu et al.				
KG	6,265,749	07/24/01	Gardner et al.				
KH	6,313,486	11/01	Kencke et al.				
KI	6,316,832	11/13/01	Tsuzuki et al.				
KJ	2002/0008234	01/02	Emrick				
KK	3,670,213	06/13/72	Nakawaga et al.				
KL	4,756,007	07/05/88	Qureshi et al.				
KM	4,773,063	09/20/88	Hunsperger et al.				
KN	5,394,489	02/28/95	Koch				
KO	5,406,202	04/11/95	Mehrgardt et al.				
KP	5,528,067	06/18/96	Farb et al.				
KQ	5,572,052	11/05/96	Kashihara et al.				
KR	5,767,543	06/16/98	Ooms et al.				
KS	6,175,497	01/16/01	Tseng et al.				
KT	6,197,503	03/06/01	Vo-Dinh et al.				
KU	6,248,459	06/19/01	Wang et al.				
KV	6,252,261	06/26/01	Usui et al.				
KW	6,255,198	07/03/01	Linthicum et al.				
KX	6,268,269	07/31/01	Lee et al.				
KY	6,291,319	09/18/01	Yu et al.				
KZ	6,316,785	11/13/01	Nunoue et al.				
LA	6,343,171	01/29/02	Yoshimura et al.				
LB	4,965,649	10/23/90	Zanio et al.				
LC	6,253,649	05/01	Kawahara et al.				
LD	6,211,096	04/01	Allman et al.				
LE	6,239,449	05/29/01	Fafard et al.				
LF	2001/0013313	08/16/01	Droopad et al.				
LG	6,184,044	02/06/01	Sone et al.				
LH	6,011,646	01/04/00	Mirkarimi et al.				
LI	5,227,196	07/13/93	Itoh				
LJ	6,150,239	11/21/00	Goesele et al.				
LK	5,441,577	08/15/95	Sasaki et al.				
LL	4,459,325	07/10/84	Nozawa et al.				
LM	4,392,297	07/12/83	Little				
LN	4,289,920	09/15/81	Hovel				
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LQ	5,514,904	05/07/96	Onga et al.				

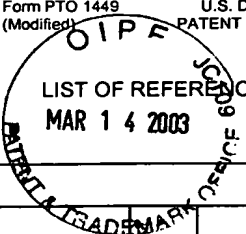
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	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
	MU	6,372,813	04/16/02	Johnson et al.			
	MV	5,608,046	03/04/97	Cook et al.			
	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/95	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
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	ND	5,541,422	07/30/96	Wolf et al.			
	NE	5,873,977	02/23/99	Desu et al.			
	NF	5,538,941	07/23/96	Findikoglu et al.			
	NG	6,046,464	04/04/00	Schetzina			
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	NP	6,011,641	01/04/00	Shin et al.			
	NQ	6,340,788 B1	01/22/02	King et al.			

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	OB 4,681,982	07/21/87	Yoshida				
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	OD 4,452,720	06/05/84	Harada et al.				
	OE 3,935,031	01/27/76	Adler				
	OF 5,760,426	06/02/98	Marx et al.				
	OG 5,053,835	10/01/91	Horikawa et al.				
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	OI 5,770,887	06/23/98	Tadatomo et al.				
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	OK 4,774,205	09/27/88	Choi et al.				
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	OO 6,367,699 B2	04/09/02	Ackley				
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	OR 5,481,102	01/02/96	Hazelrigg, Jr.				
	OS 6,134,114	10/17/00	Ungermann et al.				
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	OV 5,753,300	05/19/98	Wessels et al.				
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	PB 6,391,674 B2	05/21/02	Ziegler				
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	PI 6,087,681	06/11/00	Shakuda				
	PJ 5,132,648	07/21/92	Trinh et al.				
	PK 6,427,066	07/30/02	Grube				
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	QD	6,248,621 B1	06/19/01	Wilk et al.			
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	SC	4,146,297	03/27/79	Alferness et al.			
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	TE	4,934,777	06/19/90	Jou et al.			
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	UD	5,682,046	10/28/97	Takahashi et al.			
	UE	5,181,085	01/19/93	Moon et al.			
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	US	6,326,637 B1	12/04/01	Parkin et al.			
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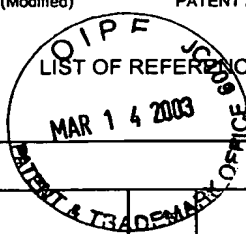
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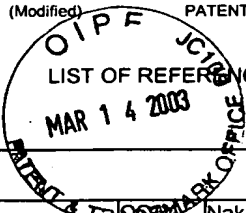
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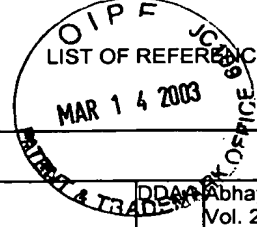
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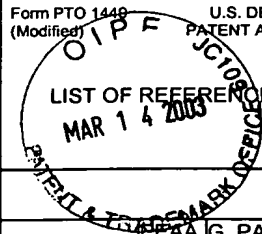
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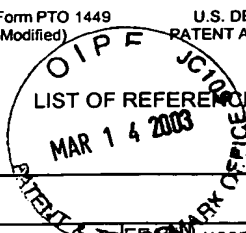
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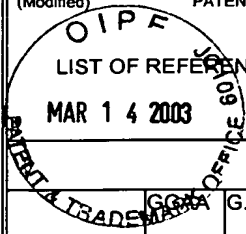
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	CAJ	WO 02/03480	01/10/02	WIPO			
	CAK	WO 02/50879	06/27/02	WIPO			
	CAL	EP 0 777 379	06/04/97	Europe			
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	CAS	EP 1 043 765	10/11/00	Europe			
	CAT	0 300 499	01/25/89	Europe			
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	CAY	63-289812	11/28/88	Japan (English Abstract only)			
	CAZ	EP 0 884 767	12/16/98	Europe			
	CBA	06-069490	03/11/94	Japan (English Abstract only)			
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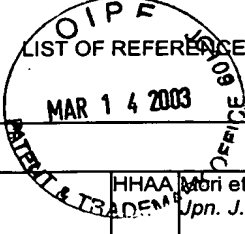
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DDAB	Abhay M. Joshi et al., "Monolithic InGaAs-on-silicon Wave Infrared Detector Arrays," <i>Intr. Society for Optical Engineering</i> , Vol. 2999, pp. 211-224.		
DDAB	Bruley et al., "Nanostructure and Chemistry of a (100)MgO/(100) GaAs Interface," <i>Appl. Phys Lett</i> , 65(5), Aug. 1994, pp. 564-566.		
DDAC	Fork et al., "Epitaxial MgO On Si(001) for Y-Ba-Cu-O Thin Film Growth by Pulsed Laser Deposition," <i>Appl. Phys Lett.</i> , 58(20), May 20, 1991, pp. 2294-2296.		
DDAD	Himpsel et al., "Dielectrics on Semiconductors," <i>Materials Science and Engineering</i> , B1(1988), pp. 9-13.		
DDAE	Li et al., "Epitaxial La _{0.67} Sr _{0.33} MnO ₃ Magnetic Tunnel Junctions," <i>J. Appl. Phys.</i> 81(8), Apr. 15, 1997, pp. 5509-5511.		
DDAF	O'Donnell et al., "Colossal Magnetoresistance Magnetic Tunnel Junctions Grown by Molecular-Beam Epitaxy," <i>Appl. Physics Letters</i> , Vol. 76, No. 14, April 3, 2000, pp. 1914-1916.		
DDAG	Mikami et al., "Formation of Si Epi/MgO-Al ₂ O ₃ Epi./SiO ₂ /Si and Its Epitaxial Film Quality," <i>Fundamental Research Laboratories and Microelectronics Laboratories</i> , pp. 31-34, 1983.		
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DDAK	R.A. Morgan et al., "Vertical-Cavity Surface-Emitting Lasers Come of Age," <i>SPIE</i> , Vol. 2683, pp. 18-29.		
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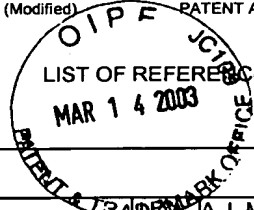
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EEAD	J.K. ABROKWAH, et al.; "A Manufacturable Complementary GaAs Process"; GaAs IC Symposium, IEEE, 1993; pp. 127-130		
EEAE	H. Nagata, "A Preliminary Consideration of the Growth Behaviour of CeO ₂ , SrTiO ₃ and SrVO ₃ Films on Si Substrate," <i>Thin Solid Films</i> , 224, 1993, pp. 1-3.		
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EEAG	Kado et al., "Heteroepitaxial Growth of SrO Films on Si Substrates," <i>J. Appl. Phys.</i> , 61(6), March 15, 1987, pp. 2398-2400.		
EEAH	H. Ishiwara et al., "Epitaxial Growth of Perovskite Type Oxide Films on Substrates"; <i>Materials Research Symposium Proceedings</i> , Vol. 220, pp. 595-600, April 29 - May 3, 1991.		
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EEAO	G. H. JIN, et al.; "PLZT Film Waveguide Mach-Zehnder Electrooptic Modulator"; <i>Journal of Lightwave Technology</i> , Vol. 18, No. 6, June 2000; pp.807-812		
EEAP	D.E. ASPNES, et al.; "Steps on (001) silicon surfaces"; <i>J. Vac. Sci. Technol. B</i> , Vol. 5, No. 4, Jul/Aug 1987; pp. 939-944		
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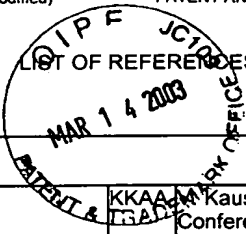
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	FFAH	James SCHELLENBERG, et al.; "Low-Loss, Planar Monolithic Baluns for K/Ka-Band Applications"; 1999 IEEE MTT-S Digest; pp.1733-1736					
	FFAI	Arnold Leitner et al; "Pulsed Laser Deposition of Superconducting Strontium Titanate Thin-Films"; ; Session K11-Thin Films and Borocarbides; Mixed Session, Wednesday Afternoon; March 19 1997; Room 1202 B, Conv. Center (Abstract)					
	FFAJ	R.D. VISPUTE; "High quality optoelectronic grade epitaxial AlN films on -Al ₂ O ₃ , Si and 6H-SiC by pulsed laser deposition"; Thin Solid Films 299 (1997), pp.94-103					
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	FFAO	Ronald W. WAYNANT, et al.; "OPTOELECTRONIC INTEGRATED CIRCUITS"; ELECTRO-OPTICS HANDBOOK, McGraw-Hill, Inc., 1994; Chapter Twenty Seven					
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	GGAO	McKee et al., " BaSi_2 and Thin Film Alkaline Earth Silicides on Silicon," <i>Appl. Phys. Lett.</i> , 63 (20), Nov. 1993, pp. 2818-2820.					
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	GGAQ	Brian A. FLOYD, et al.; "The projected Power Consumption of a Wireless Clock Distribution System and Comparison to Conventional Distribution Systems"; IEEE, 1999; pp. IITC99-249-IITC99-250					
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	HHAH	Wenhua Zhu et al.; "Molecular Beam Epitaxy of GaAs on Si-on-Insulator"; <i>320 Applied Physics Letters</i> 59(1991) 8 July No. 2; pp. 210-212					
	HHAI	Umesh K. Mishra et al; "Oxide Based Compound Semiconductor Electronics"; <i>Electron Devices Meeting; 1997; Technical Digest, International; Washington, D.C.</i> ; 7-10 December 1997; pp. 545-548					
	HHAJ	J.M. Daughton et al.; "Applications of Spin Dependent Transport Materials"; <i>J. Phys. D. Appl. Phys.</i> 32(1999) R169-R177					
	HHAK	Wei Zhang et al.; "Stress Effect and Enhanced Magnetoresistance in La _{0.67} Ca _{0.33} MnO _{3-δ} Films"; <i>Physical Review, B. Condensed Matter; American Institute of Physics</i> ; Vol. 58, No. 21, Part 1; December 1, 1998; pp. 14143-14146					
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